

C2M0045170P

Silicon Carbide Power MOSFET
C2M™ MOSFET Technology
N-Channel Enhancement Mode

Features

- 2nd generation SiC MOSFET technology
- Optimized package with separate driver source pin
- 8mm of creepage distance between drain and source
- High blocking voltage with low On-Resistance
- High speed switching with low capacitances
- Resistant to latch-up
- Halogen Free, RoHS Compliant

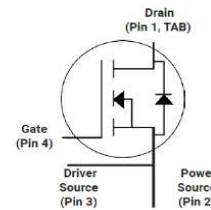
Benefits

- Reduce switching losses and minimize gate ringing
- Higher system efficiency
- Reduce cooling requirements
- Increase power density
- Increase system switching frequency

Applications

- Solar inverters
- Switch Mode Power Supplies
- High voltage DC/DC converters
- Motor drive
- Pulsed power applications

Package



Part Number	Package	Marking
C2M0045170P	TO-247-4L	C2M0045170P

Maximum Ratings ($T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{DSmax}	Drain - Source Voltage	1700	V	$V_{GS} = 0\text{ V}, I_D = 100\ \mu\text{A}$	
V_{GSmax}	Gate - Source Voltage	-10/+25	V	Absolute maximum values, AC ($f > 1\text{ Hz}$)	Note: 1
V_{GSop}	Gate - Source Voltage	-5/+20	V	Recommended operational values	Note: 2
I_D	Continuous Drain Current	75	A	$V_{GS} = 20\text{ V}, T_C = 25^\circ\text{C}$	Fig. 19
		48		$V_{GS} = 20\text{ V}, T_C = 100^\circ\text{C}$	
$I_{D(pulse)}$	Pulsed Drain Current	160	A	Pulse width t_p limited by T_{Jmax}	Fig. 22
P_D	Power Dissipation	338	W	$T_C = 25^\circ\text{C}, T_J = 150^\circ\text{C}$	Fig. 20
T_J, T_{stg}	Operating Junction and Storage Temperature	-40 to +150	$^\circ\text{C}$		
T_L	Solder Temperature	260	$^\circ\text{C}$	1.6mm (0.063") from case for 10s	

Note (1): When using MOSFET Body Diode $V_{GSmax} = -5\text{V}/+25\text{V}$

Note (2): MOSFET can also safely operate at 0/+20V

Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	1700			V	$V_{GS} = 0\text{ V}, I_D = 100\ \mu\text{A}$	
$V_{GS(th)}$	Gate Threshold Voltage	2.0	3.0	4	V	$V_{DS} = V_{GS}, I_D = 18\text{mA}$	Fig. 11
			2.5		V	$V_{DS} = V_{GS}, I_D = 18\text{mA}, T_J = 150^\circ\text{C}$	
I_{DSS}	Zero Gate Voltage Drain Current		2	100	μA	$V_{DS} = 1700\text{ V}, V_{GS} = 0\text{ V}$	
I_{GSS}	Gate-Source Leakage Current			600	nA	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$	
$R_{DS(on)}$	Drain-Source On-State Resistance		40	70	m Ω	$V_{GS} = 20\text{ V}, I_D = 50\text{ A}$	Fig. 4,5,6
			80			$V_{GS} = 20\text{ V}, I_D = 50\text{ A}, T_J = 150^\circ\text{C}$	
g_{fs}	Transconductance		24.7		S	$V_{DS} = 20\text{ V}, I_{DS} = 50\text{ A}$	Fig. 7
			23.4			$V_{DS} = 20\text{ V}, I_{DS} = 50\text{ A}, T_J = 150^\circ\text{C}$	
C_{iss}	Input Capacitance		3455		pF	$V_{GS} = 0\text{ V}$	Fig. 17,18
C_{oss}	Output Capacitance		171			$V_{DS} = 1200\text{ V}$	
C_{rss}	Reverse Transfer Capacitance		6.7			$f = 1\text{ MHz}$	
E_{oss}	C_{oss} Stored Energy		139		μJ	$V_{AC} = 25\text{ mV}$	Fig 16
$C_{o(er)}$	Effective Output Capacitance (Energy Related)		188		pF	$V_{GS} = 0\text{ V}, V_{DS} = 0 \dots 1200\text{V}$	Note: 3
$C_{o(tr)}$	Effective Output Capacitance (Time Related)		255				
E_{ON}	Turn-On Switching Energy (SiC Diode FWD)		0.52		mJ	$V_{DS} = 1200\text{ V}, V_{GS} = -5/20\text{ V},$ $I_D = 50\text{ A}, R_{G(ext)} = 2.5\ \Omega, L = 99\ \mu\text{H},$ $T_J = 150^\circ\text{C},$ using SiC Diode as FWD	Fig. 26, 29b Note 2
E_{OFF}	Turn Off Switching Energy (SiC Diode FWD)		0.43				
E_{ON}	Turn-On Switching Energy (Body Diode FWD)		2.0		mJ	$V_{DS} = 1200\text{ V}, V_{GS} = -5/20\text{ V},$ $I_D = 50\text{ A}, R_{G(ext)} = 2.5\ \Omega, L = 99\ \mu\text{H},$ $T_J = 150^\circ\text{C},$ using MOSFET as FWD	Fig. 26, 29a Note 2
E_{OFF}	Turn Off Switching Energy (Body Diode FWD)		0.31				
$t_{d(on)}$	Turn-On Delay Time		15		ns	$V_{DD} = 1200\text{ V}, V_{GS} = -5/20\text{ V}$ $I_D = 50\text{ A},$ $R_{G(ext)} = 2.5\ \Omega,$ Timing relative to V_{DS} Inductive load	Fig. 27, 29 Note 2
t_r	Rise Time		18				
$t_{d(off)}$	Turn-Off Delay Time		34				
t_f	Fall Time		12				
$R_{G(int)}$	Internal Gate Resistance		1.3		Ω	$f = 1\text{ MHz}, V_{AC} = 25\text{ mV}$	
Q_{gs}	Gate to Source Charge		46		nC	$V_{DS} = 1200\text{ V}, V_{GS} = -5/20\text{ V}$ $I_D = 50\text{ A}$ Per IEC60747-8-4 pg 21	Fig. 12
Q_{gd}	Gate to Drain Charge		71				
Q_g	Total Gate Charge		204				

Note (3): $C_{o(er)}$, a lumped capacitance that gives same stored energy as C_{oss} while V_{ds} is rising from 0 to 1200V
 $C_{o(tr)}$, a lumped capacitance that gives same charging time as C_{oss} while V_{ds} is rising from 0 to 1200V

Reverse Diode Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_{SD}	Diode Forward Voltage	3.8		V	$V_{GS} = -5\text{ V}, I_{SD} = 25\text{ A}$	Fig. 8, 9, 10 Note 1
		3.4		V	$V_{GS} = -5\text{ V}, I_{SD} = 25\text{ A}, T_J = 150\text{ }^\circ\text{C}$	
I_S	Continuous Diode Forward Current		76	A	$V_{GS} = -5\text{ V}, T_C = 25\text{ }^\circ\text{C}$	Note 1
$I_{S,pulse}$	Diode pulse Current		160	A	$V_{GS} = -5\text{ V}$, pulse width t_p limited by T_{jmax}	Note 1
t_{rr}	Reverse Recovery Time	44		ns	$V_{GS} = -5\text{ V}, I_{SD} = 50\text{ A}, V_R = 1200\text{ V}$ $dif/dt = 3000\text{ A}/\mu\text{s}, T_J = 150\text{ }^\circ\text{C}$	
Q_{rr}	Reverse Recovery Charge	1.9		μC		
I_{rrm}	Peak Reverse Recovery Current	64		A		
t_{rr}	Reverse Recovery Time	25		ns	$V_{GS} = -5\text{ V}, I_{SD} = 50\text{ A}, V_R = 1200\text{ V}$ $dif/dt = 13450\text{ A}/\mu\text{s}, T_J = 150\text{ }^\circ\text{C}$	
Q_{rr}	Reverse Recovery Charge	2.4		μC		
I_{rrm}	Peak Reverse Recovery Current	166		A		

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	0.22	0.37	$^\circ\text{C}/\text{W}$		Fig. 21
$R_{\theta JC}$	Thermal Resistance from Junction to Ambient		40			

Typical Performance

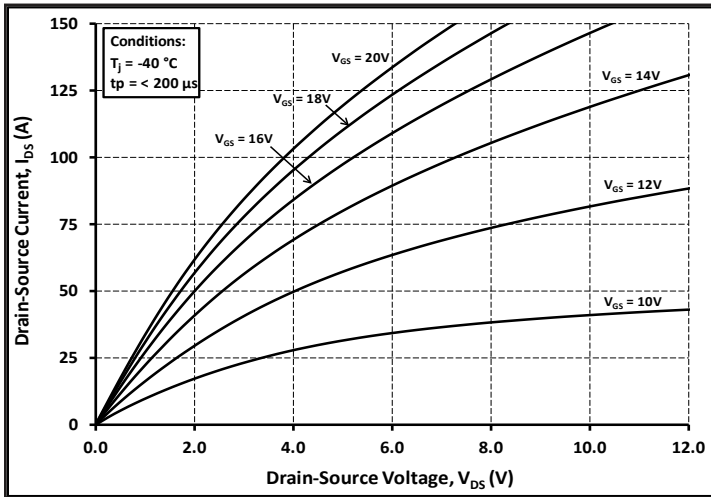


Figure 1. Output Characteristics $T_J = -40\text{ }^\circ\text{C}$

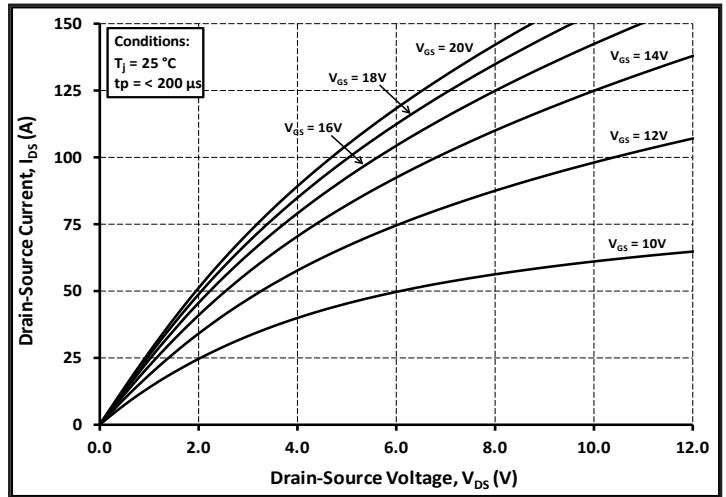


Figure 2. Output Characteristics $T_J = 25\text{ }^\circ\text{C}$

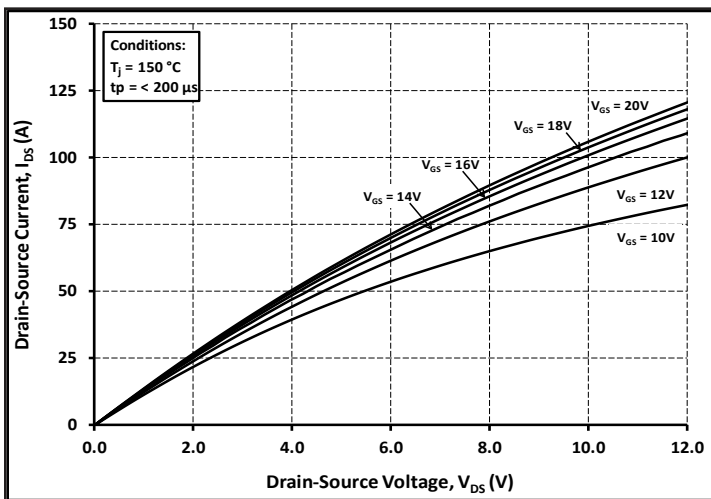


Figure 3. Output Characteristics $T_J = 150\text{ }^\circ\text{C}$

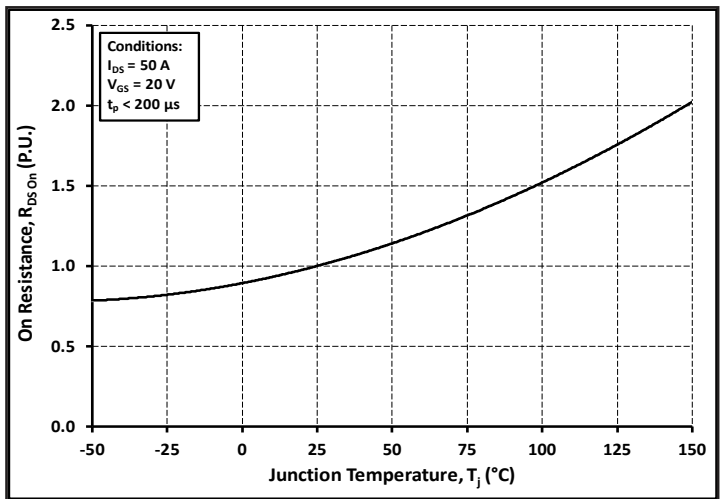


Figure 4. Normalized On-Resistance vs. Temperature

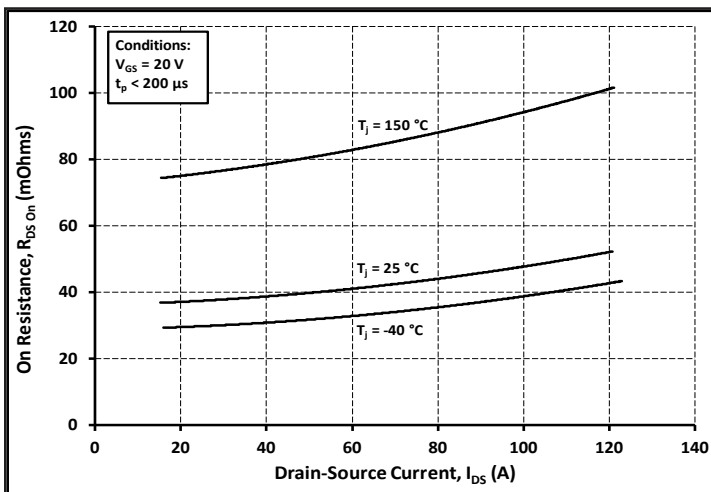


Figure 5. On-Resistance vs. Drain Current For Various Temperatures

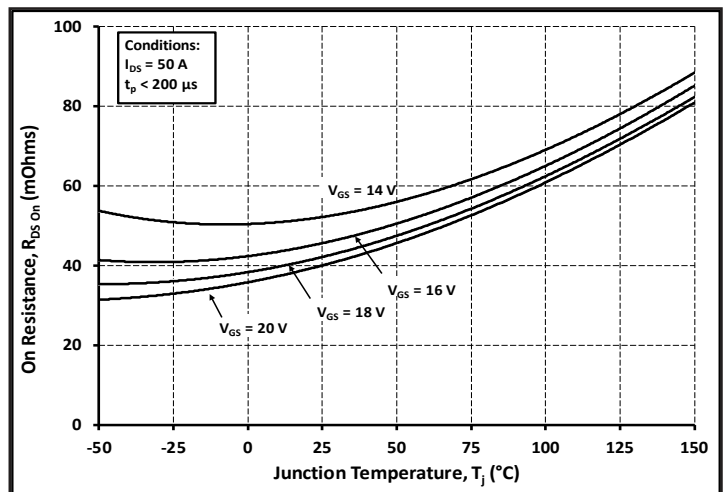


Figure 6. On-Resistance vs. Temperature For Various Gate Voltage

Typical Performance

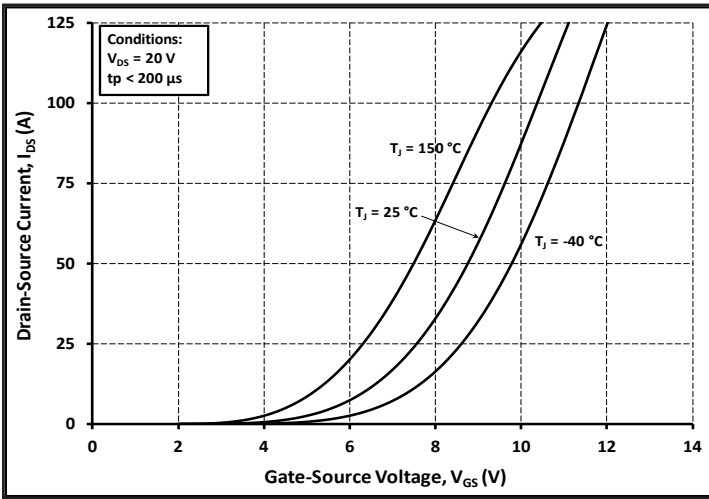


Figure 7. Transfer Characteristic For Various Junction Temperatures

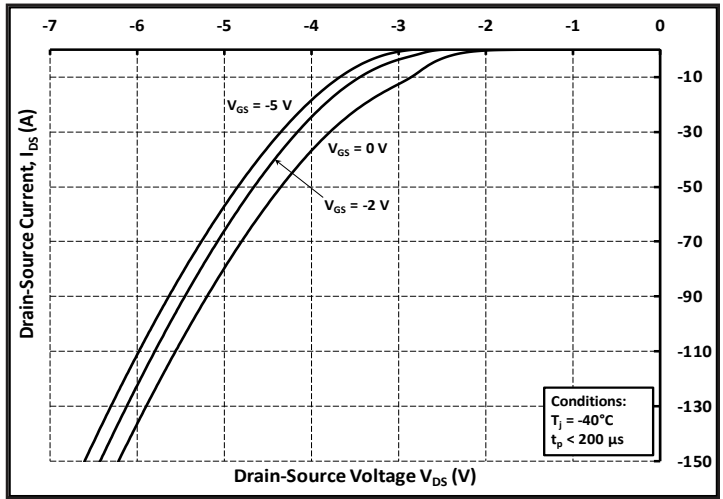


Figure 8. Body Diode Characteristic at -40 °C

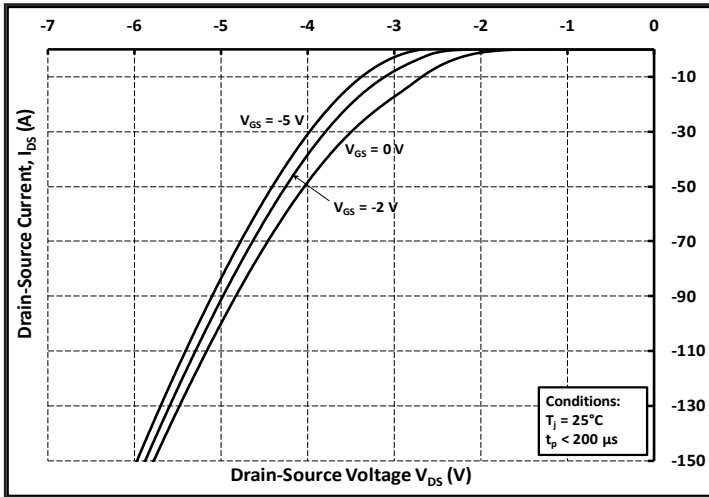


Figure 9. Body Diode Characteristic at 25 °C

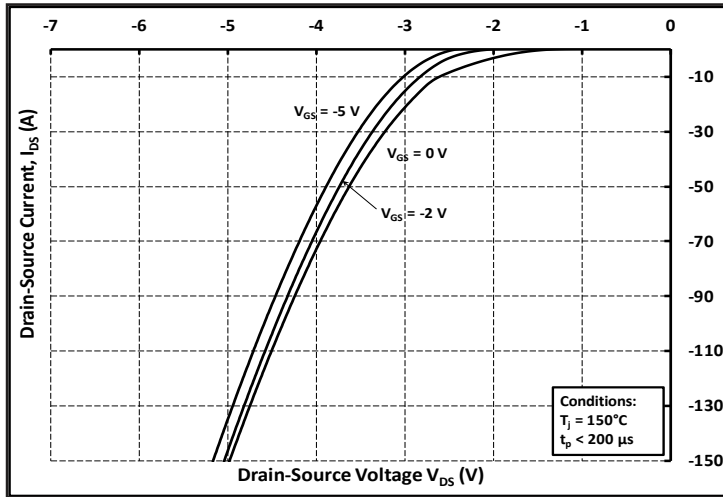


Figure 10. Body Diode Characteristic at 150 °C

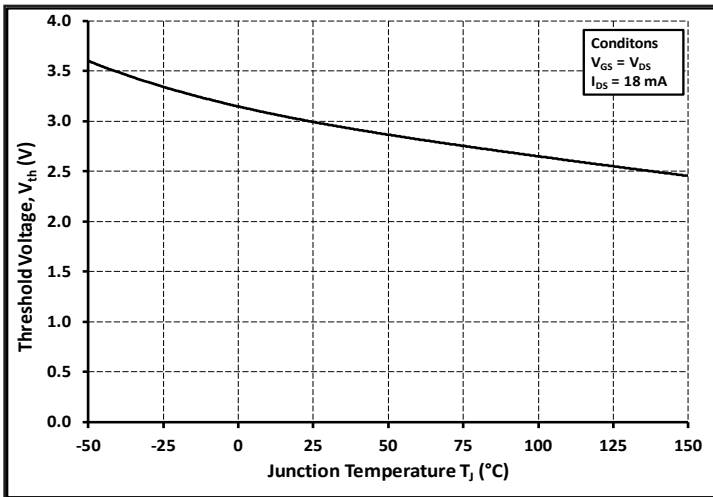


Figure 11. Threshold Voltage vs. Temperature

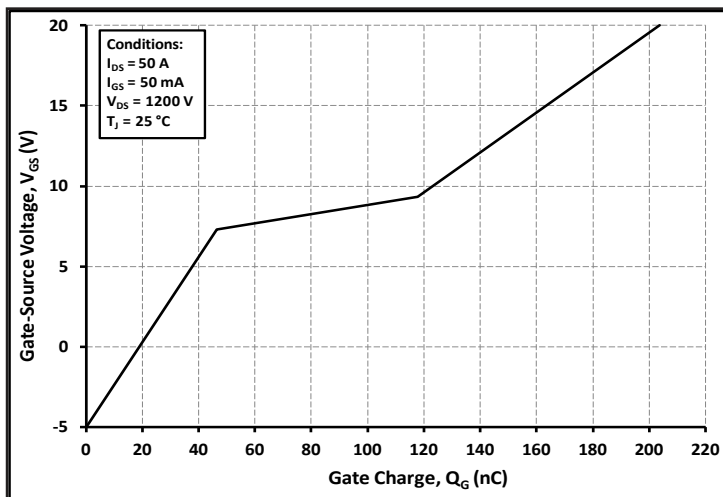


Figure 12. Gate Charge Characteristic

Typical Performance

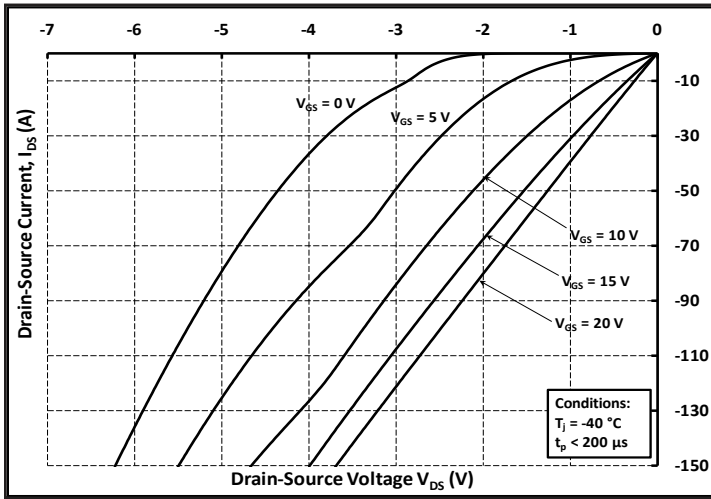


Figure 13. 3rd Quadrant Characteristic at -40 °C

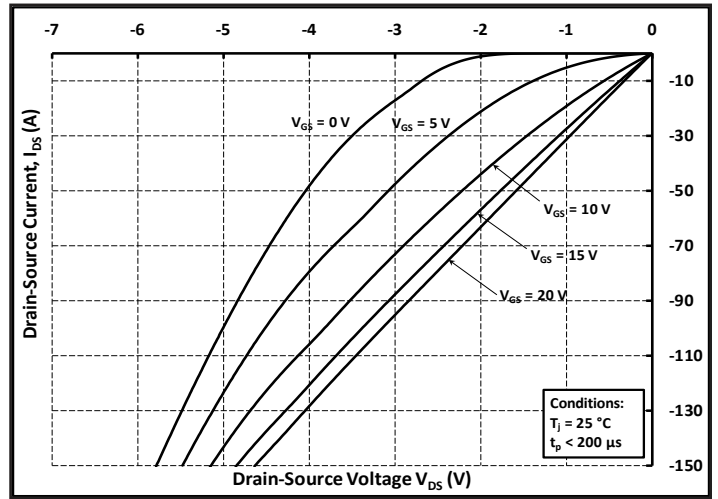


Figure 14. 3rd Quadrant Characteristic at 25 °C

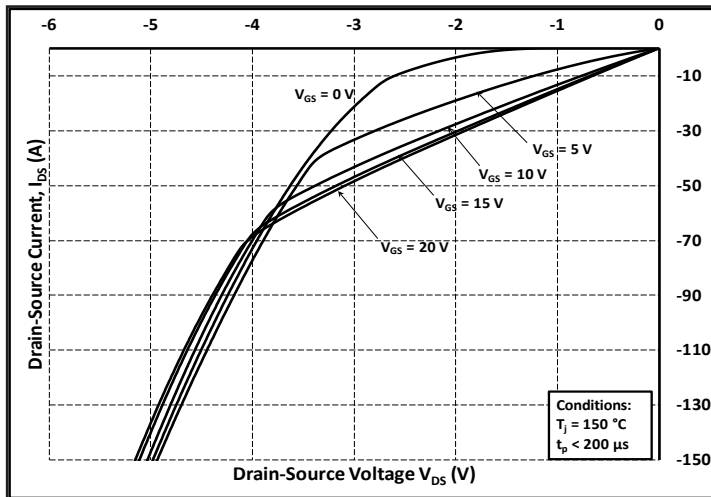


Figure 15. 3rd Quadrant Characteristic at 150 °C

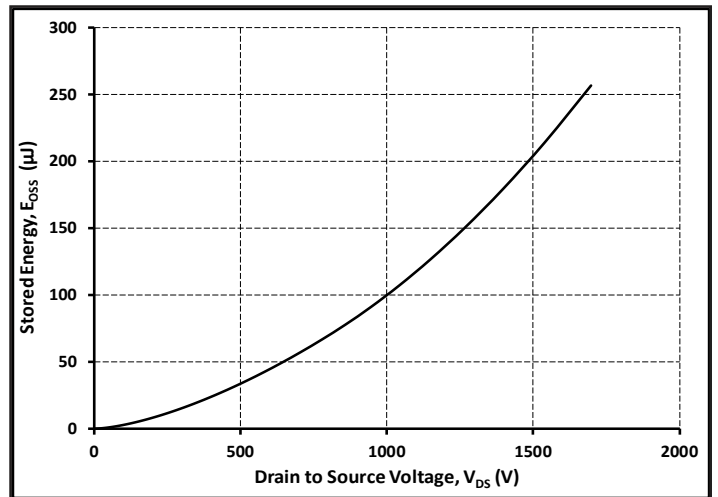


Figure 16. Output Capacitor Stored Energy

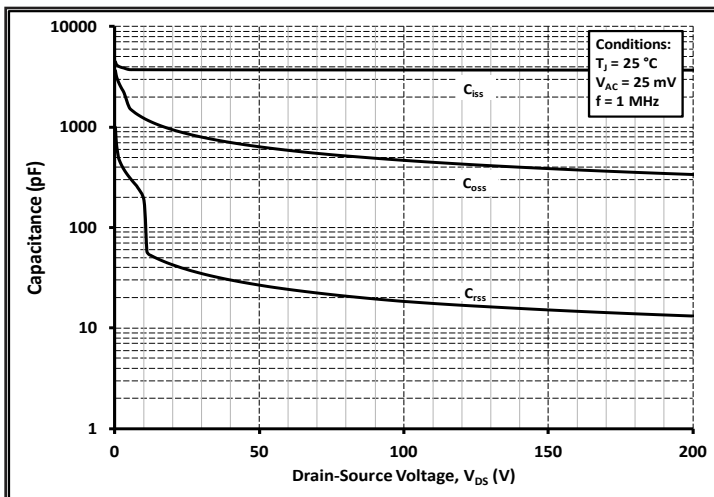


Figure 17. Capacitances vs. Drain-Source Voltage (0-200 V)

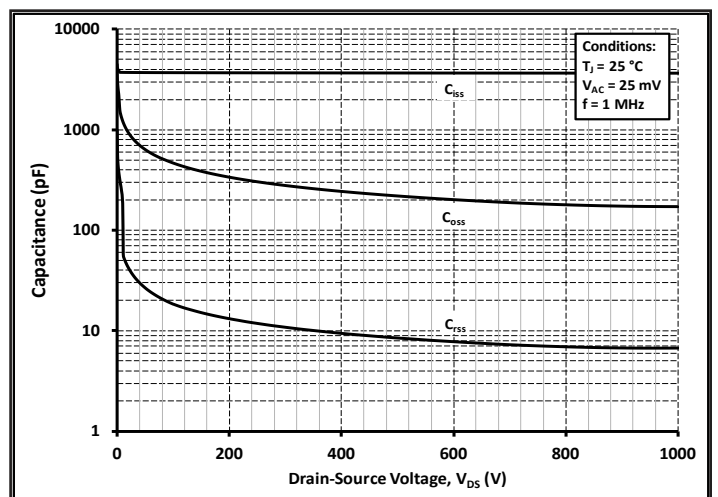


Figure 18. Capacitances vs. Drain-Source Voltage (0-1000 V)

Typical Performance

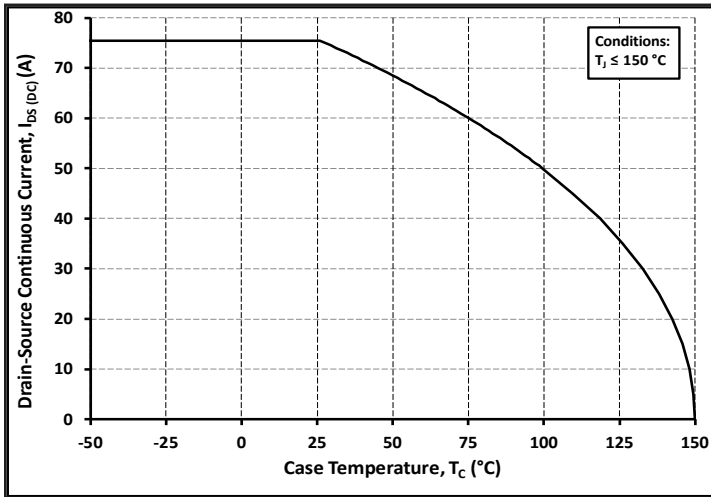


Figure 19. Continuous Drain Current Derating vs. Case Temperature

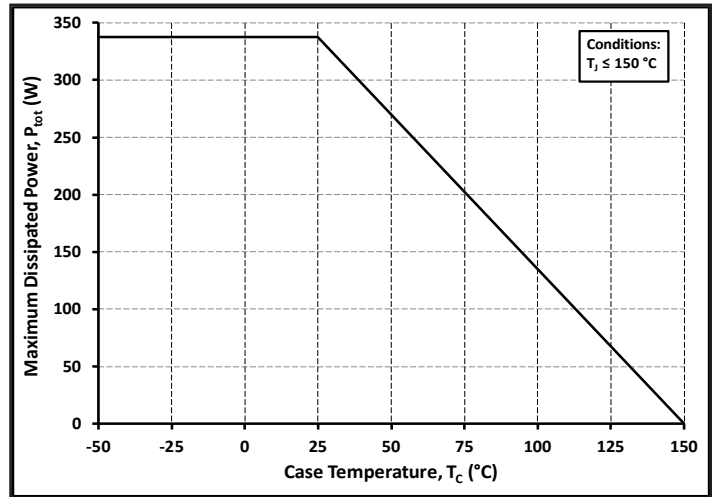


Figure 20. Maximum Power Dissipation Derating vs. Case Temperature

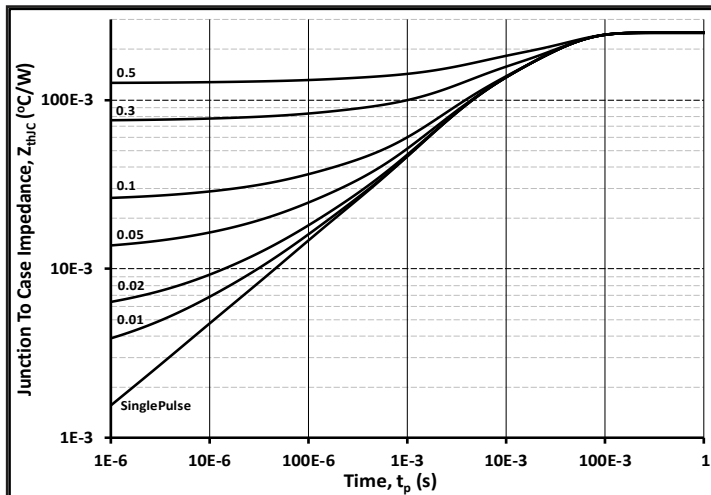


Figure 21. Transient Thermal Impedance (Junction - Case)

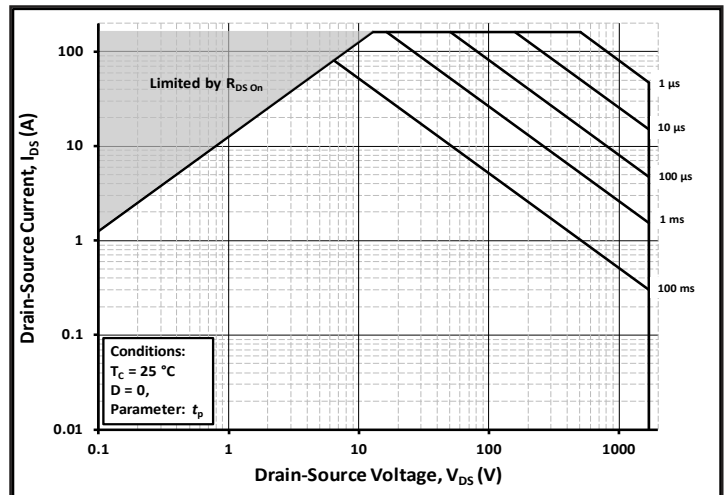


Figure 22. Safe Operating Area

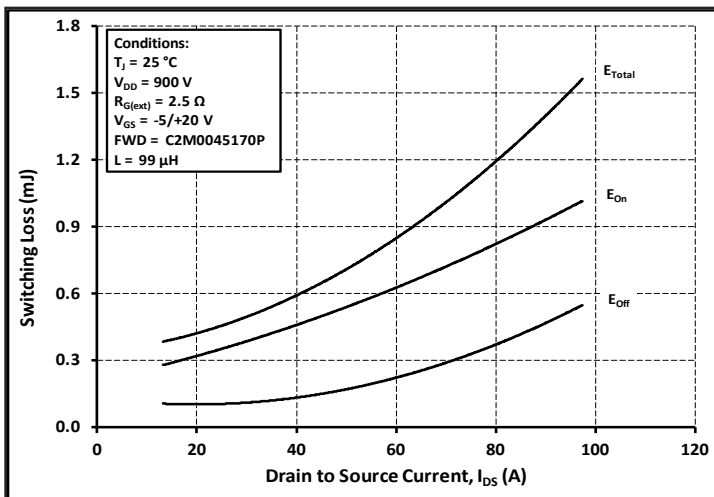


Figure 23. Clamped Inductive Switching Energy vs. Drain Current ($V_{DD} = 900V$)

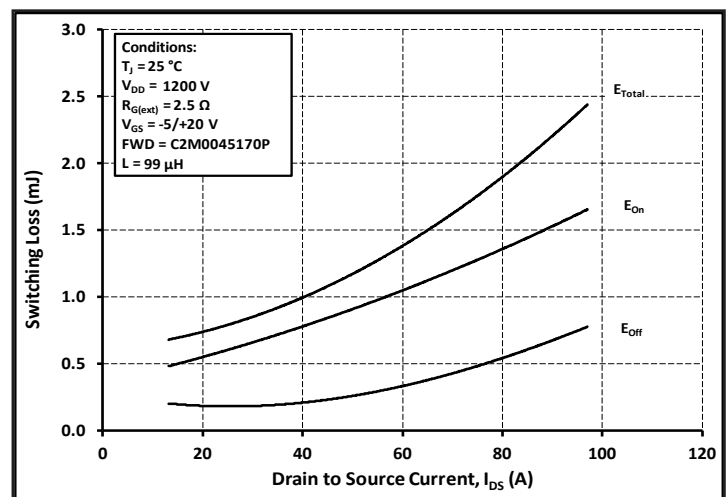


Figure 24. Clamped Inductive Switching Energy vs. Drain Current ($V_{DD} = 1200V$)

Typical Performance

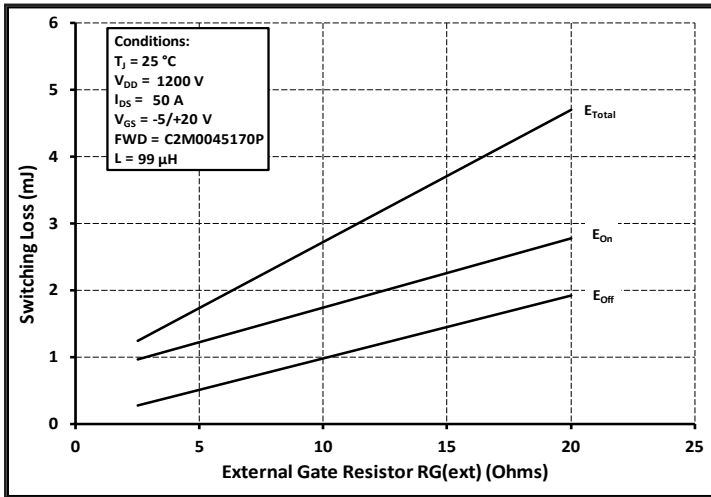


Figure 25. Clamped Inductive Switching Energy vs. $R_{G(ext)}$

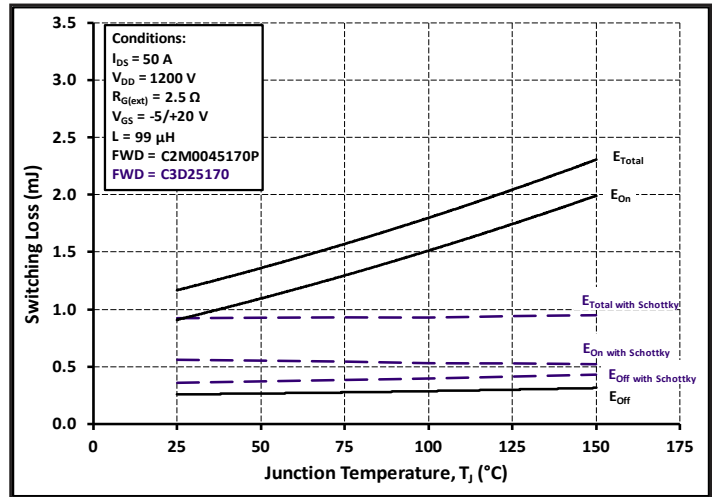


Figure 26. Clamped Inductive Switching Energy vs. Temperature

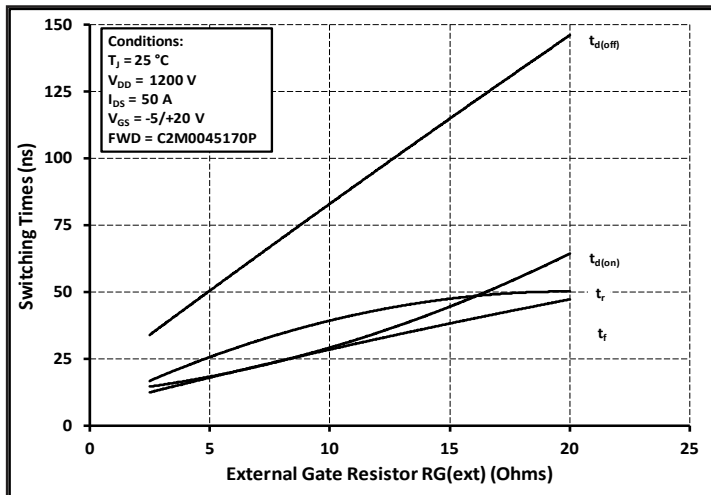


Figure 27. Switching Times vs. $R_{G(ext)}$

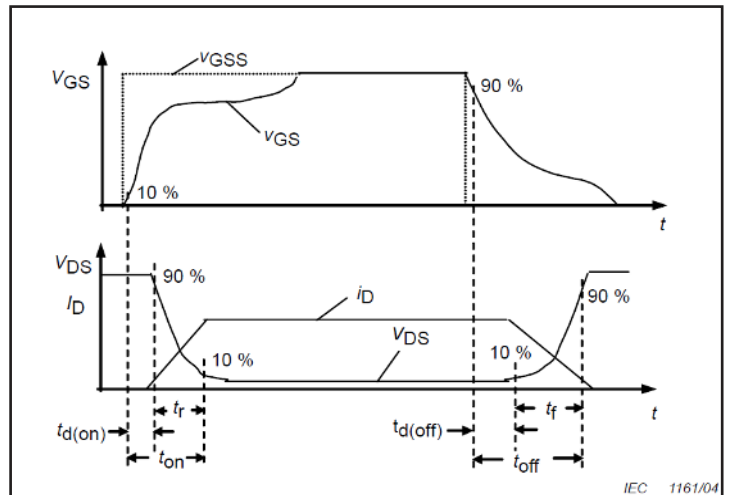


Figure 28. Switching Times Definition

Test Circuit Schematic

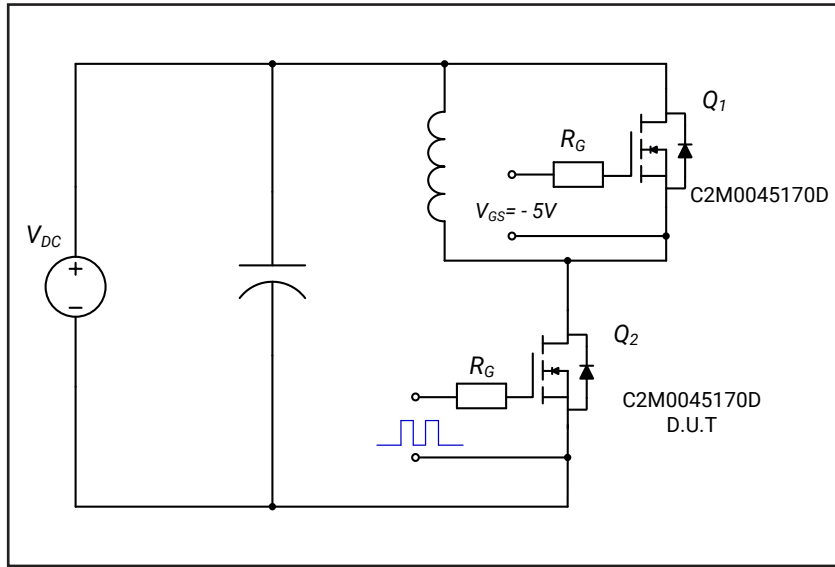


Figure 29a. Clamped Inductive Switching Test Circuit using MOSFET intrinsic body diode

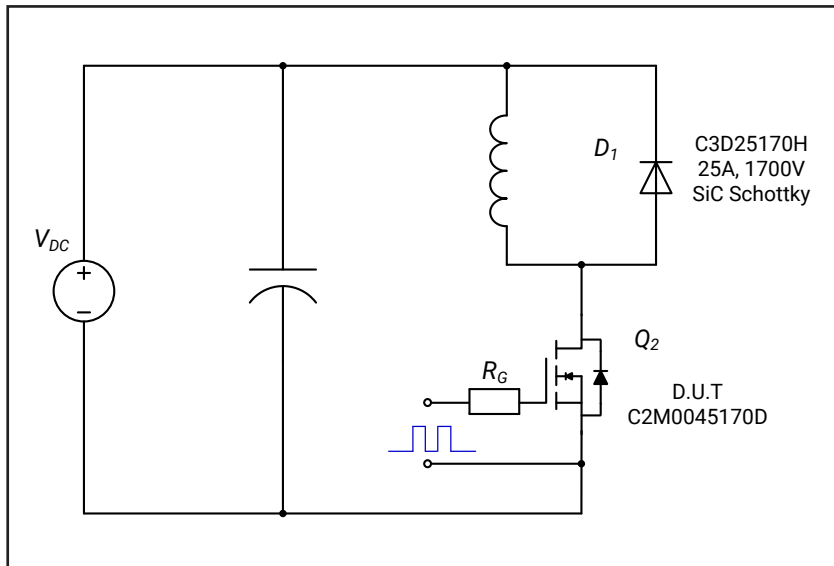
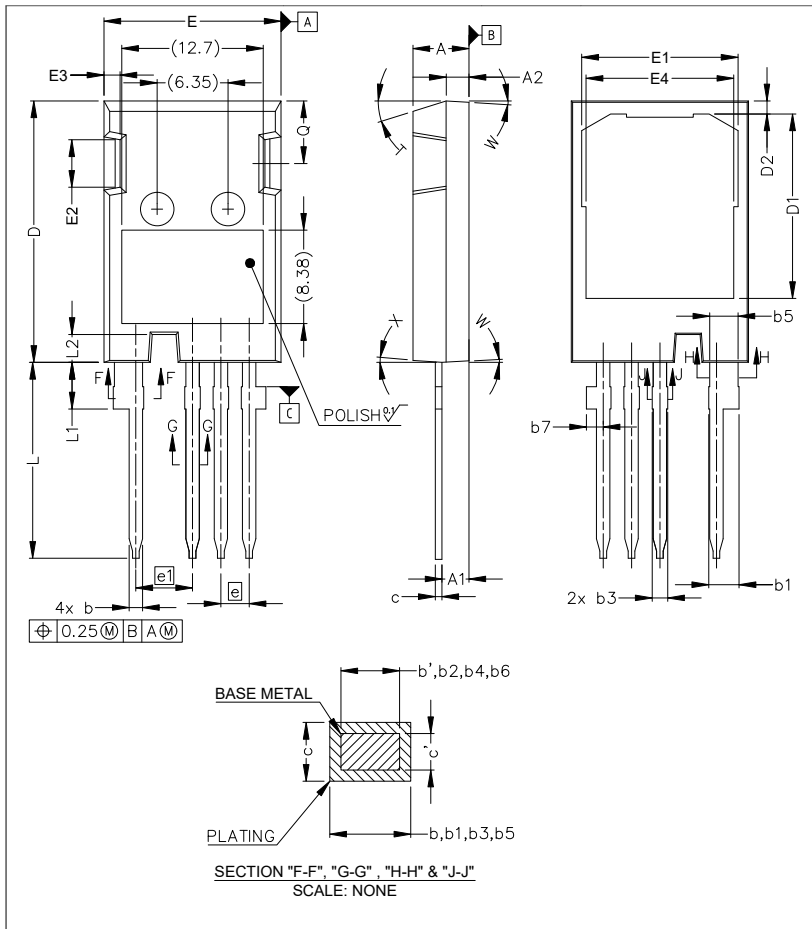


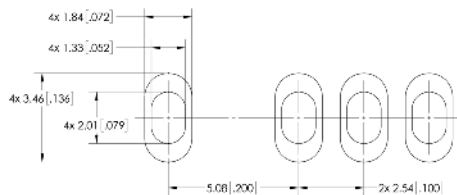
Figure 29b. Clamped Inductive Switching Test Circuit using SiC Schottky diode

Package Dimensions



SYM	MILLIMETERS	
	MIN	MAX
A	4.83	5.21
A1	2.29	2.54
A2	1.91	2.16
b'	1.07	1.28
b	1.07	1.33
b1	2.39	2.94
b2	2.39	2.84
b3	1.07	1.60
b4	1.07	1.50
b5	2.39	2.69
b6	2.39	2.64
b7	1.30	1.70
c'	0.55	0.65
c	0.55	0.68
D	23.30	23.60
D1	16.25	17.65
D2	0.95	1.25
E	15.75	16.13
E1	13.10	14.15
E2	3.68	5.10
E3	1.00	1.90
E4	12.38	13.43
e	2.54 BSC	
e1	5.08 BSC	
N*	4	
L	17.31	17.82
L1	3.97	4.37
L2	2.35	2.65
Q	5.49	6.00
T	17.5° REF.	
W	3.5° REF.	
X	4° REF.	

Recommended Solder Pad Layout



Revision history

Document Version	Date of release	Description of changes
Rev -	April - 2018	Initial datasheet
Rev 1	NA	Revision 1 not released.
Rev 2	May - 2022	Added effective output capacitance, Typical values updated to support PCN-1278.

Note:

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